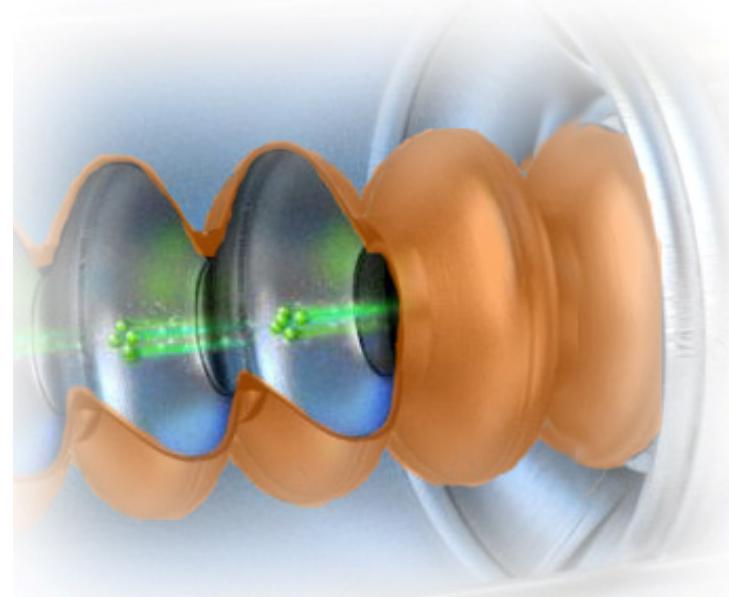


# Progress With Nb Hipims Films on 1.3 GHz Cu Cavities

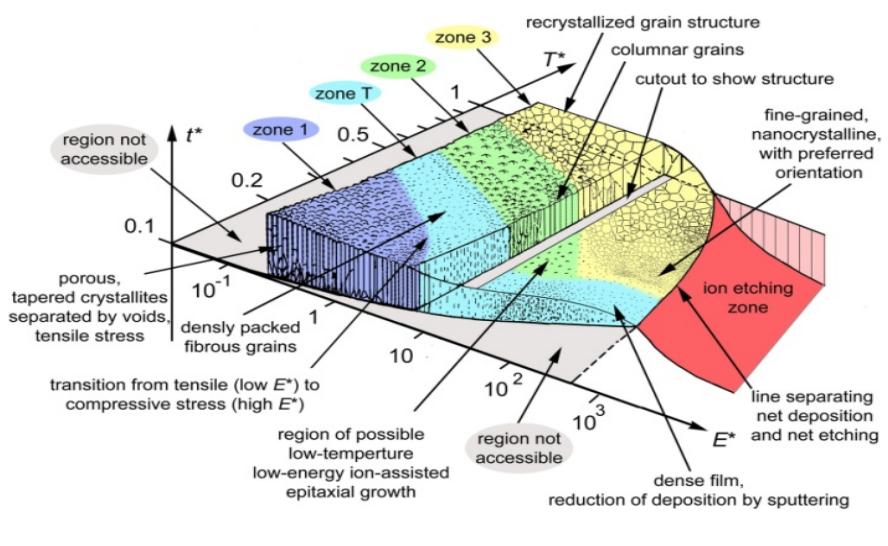
Matthew C. Burton

Presented by A.-M. Valente-Feliciano

M.C. Burton, A.-M. Valente-Feliciano, A. D. Palczewski, C. E. Reece

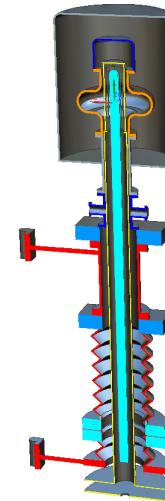


# Energetic Condensation via HiPIMS



Anders, André. "A structure zone diagram including plasma-based deposition and ion etching." *Thin Solid Films* 518.15 (2010): 4087-4090.

## High Power Impulse Magnetron Sputtering (HiPIMS)



Requires working gas

Multiply charged ions of Nb & Kr

Presence of neutrals

Controllable

deposition energy

with Bias voltage

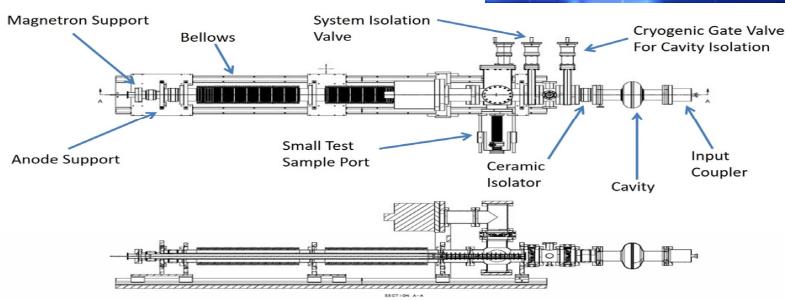
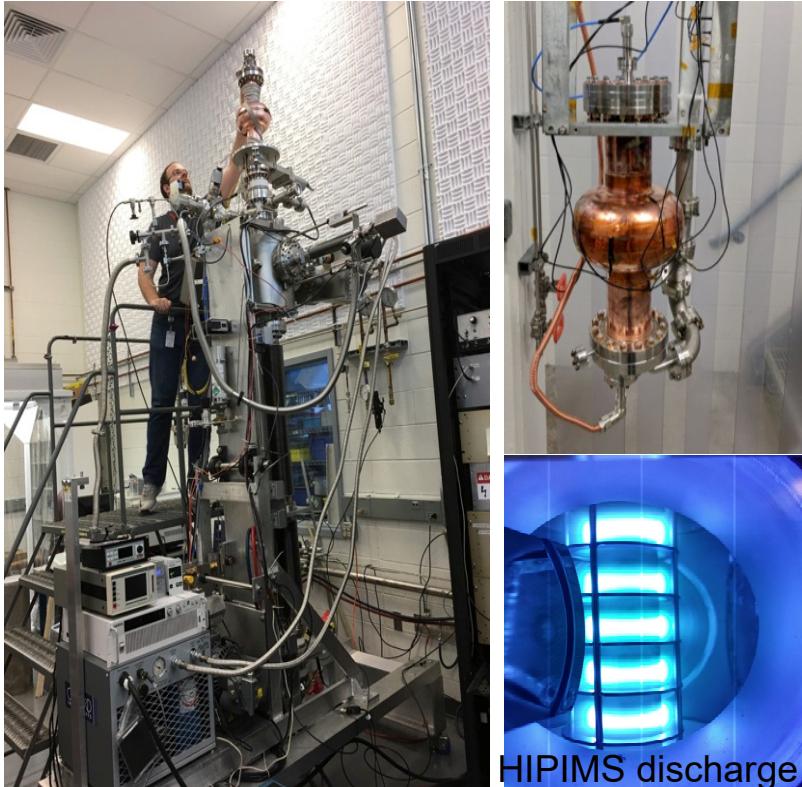
Excellent bonding

No macro particles

Ease of cavity configuration

# HiPIMS Cavity Coating System

Vertical coating system 1.3 GHz Nb/Cu cavity



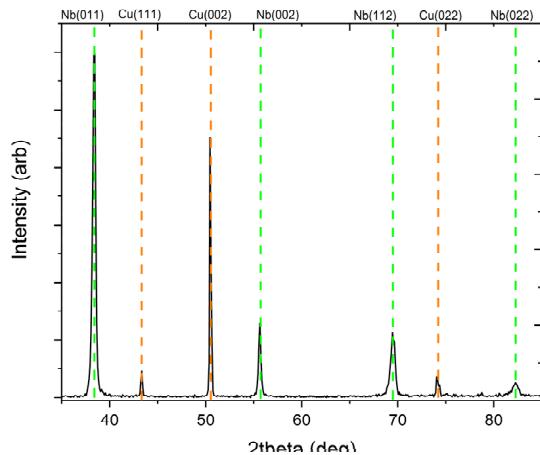
- Movable cylindrical Nb cathode
- Background pressure in  $10^{-9}$ - $10^{-10}$  Torr
- Coating temperatures up to 400 ° C under external nitrogen flow
- Kr atmosphere

## System upgrades

- Tripled Pulse Power Capability
- Permanent Vertical System Operation
- New Nb cathode with proper length
- Cavity support during bake-out

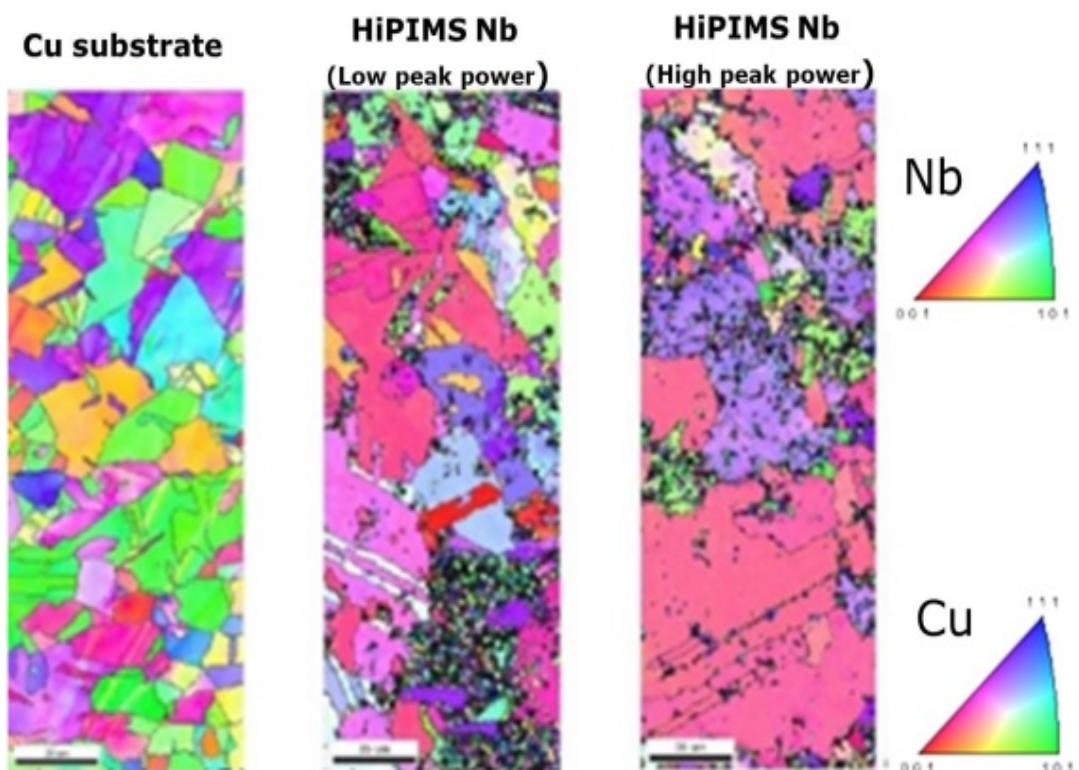
System re-commissioned  
June 2018

# HiPIMS Nb films - Structure



Typical polycrystalline texture dominated by the Nb (011) phase. Average grain sizes determined with the Scherrer equation and the FWHM of the Nb (011) peak.

XRD



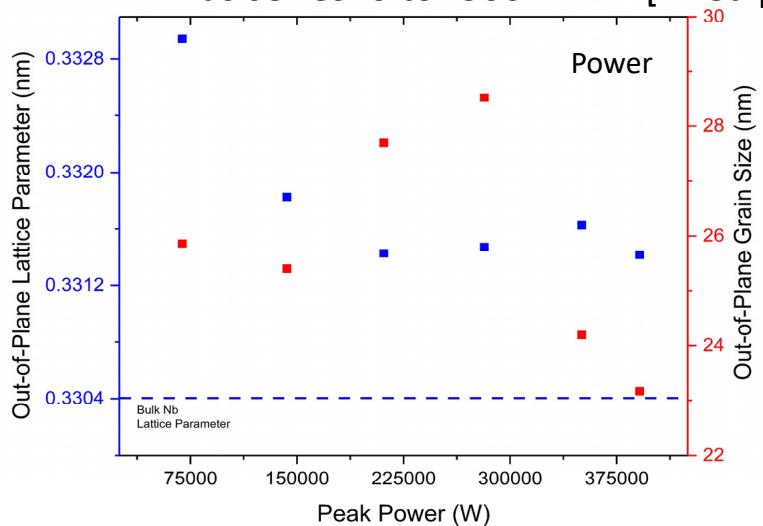
EBSD

# HiPIMS Nb films – Structure & roughness

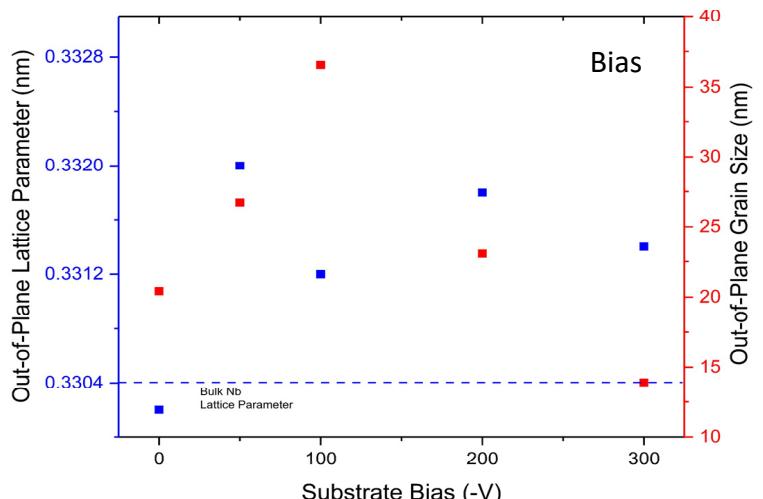
2 sample series performed to correlate deposition parameters to structure

◻ Power series: 69 to 391 kW [Fixed bias -100 V]

◻ Bias series: 0 to -300 V [Fixed peak power 220 kW]



Both peak power and applied bias voltage series resulted with lattice parameters larger than bulk  
a decreasing trend with peak power and an increasing trend with bias.  
0 V bias leads to a smaller than bulk lattice parameter (0.3304 nm) flipping the stress present in the film?

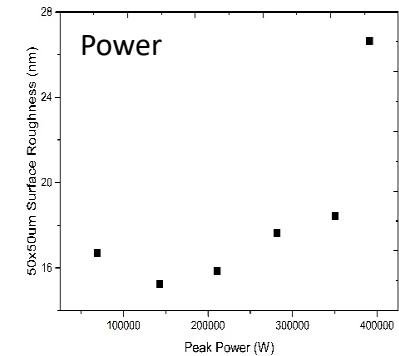
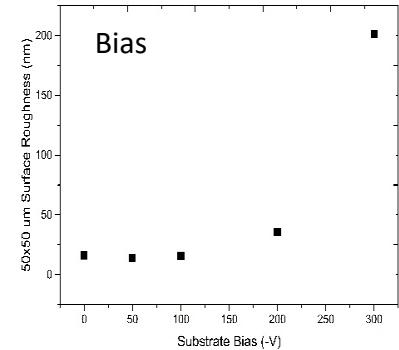


increasing surface roughness with increasing power and bias independently

Results indicate ability/need to engineer film properties throughout growth

Optimized bias will have to be a compromise for ion energy high enough to insure good adhesion while keeping control over final RF surface roughness

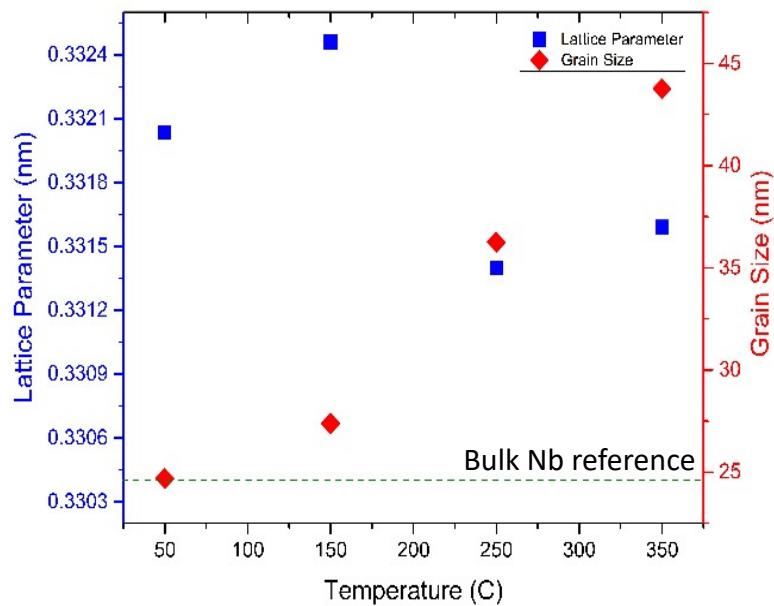
RMS roughness  
50×50  $\mu\text{m}$  scale



# HiPIMS Nb films - Structure

☐ Temperature series: 50 to 350 °C [Fixed bias -25-35 V, power 350-400 kW ]

Temperature (C)	Peak Power (kW)	Applied Substrate Bias Voltage (V)	Out-of-Plane Lattice Parameter (nm)	Out-of-Plane Grain Size (nm)
350	332	25	0.3316	43.77
250	360	35	0.3314	36.24
150	377	25	0.3325	27.38
50	400	25	0.3320	24.69



Consistency with previous sample series  
Reproducible film quality



# 1.3 GHz Nb/Cu Cavity Procedure

## Surface Preparation

- SUBU 5
- 15 to 30  $\mu\text{m}$  removal
- HPWR
- Drying with methanol sheeting
- Assembly in ISO-4 clean room
- Slow pump down
- Bake-out 24 h

## Coating

- $T_{\text{bake/coating}} = 350 \text{ or } 150^\circ\text{C}$
- Target-substrate distance = 10 cm  
[samples & equator]
- Film thickness  $\sim 1.5 \mu\text{m}$
- $f = 83 \text{ Hz}$
- Pulse width = 110  $\mu\text{s}$
- $P_{\text{Kr}} = 4.2 \text{ mTorr}$
- Bias = -100 V or -25 V
- Peak power = 220 kW

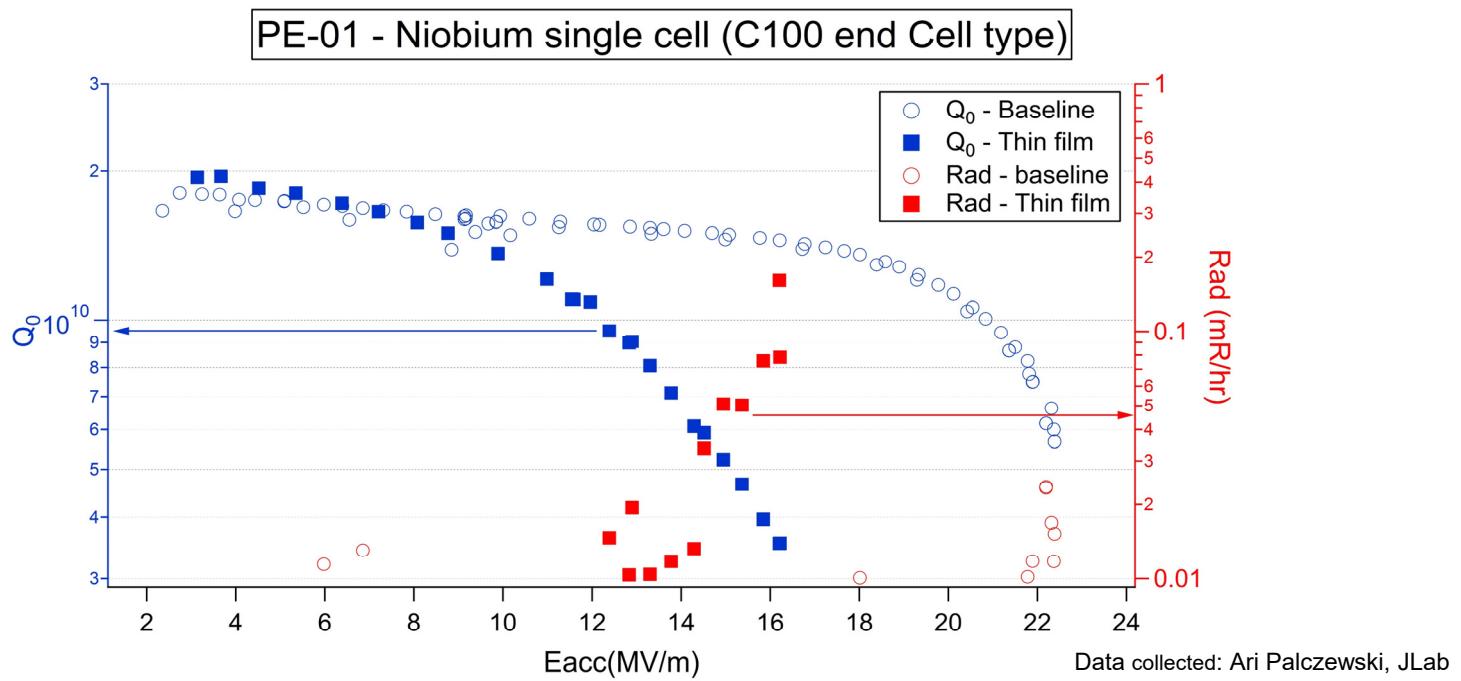
## Preparation for RF test

- HPWR
- Drying in ISO-4 cleanroom
- Assembly in ISO-4 clean room
- Assembly on test stand
- Slow pump down

# HiPIMS Cavities - 1<sup>st</sup> RF Tests on bulk Nb

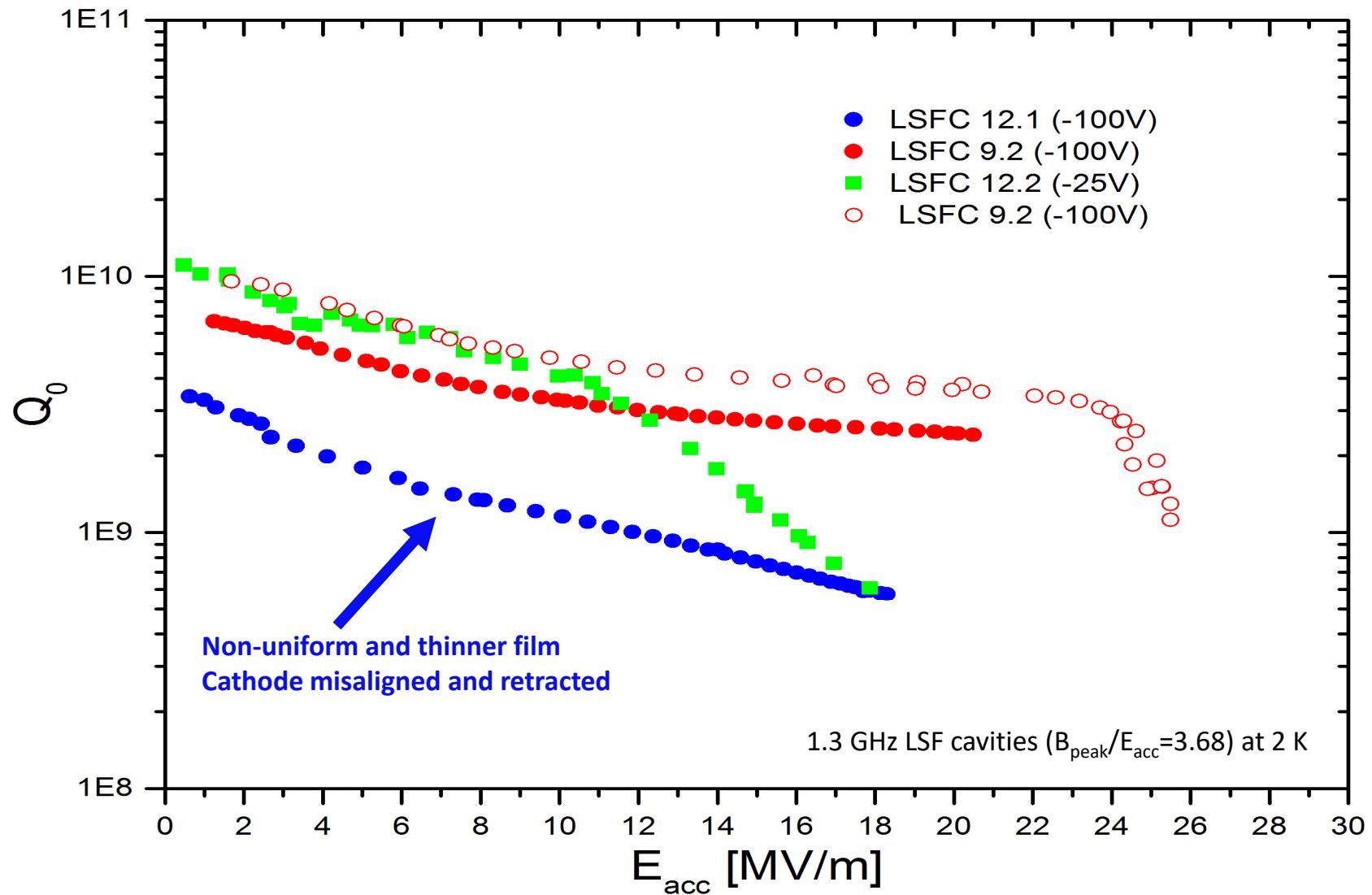
- Test of deposition system capabilities

Coated 1.5 GHz C100 end cell bulk Nb cavity

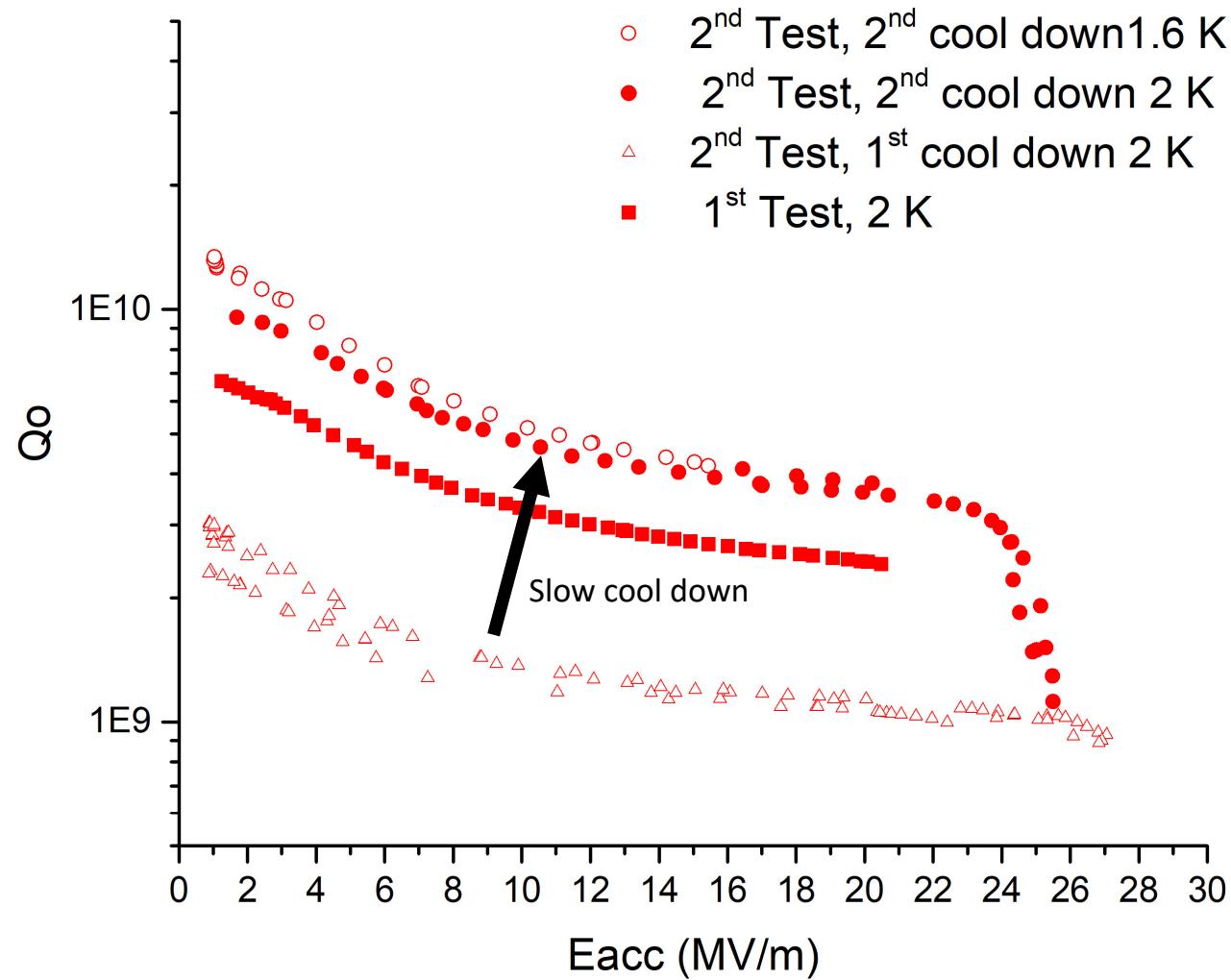


- 1<sup>st</sup> coatings (no HPR before RF test)
  - comparable to bulk performance up to 10 MV/m then heavy field emission

# HiPIMS Cavities RF Behavior



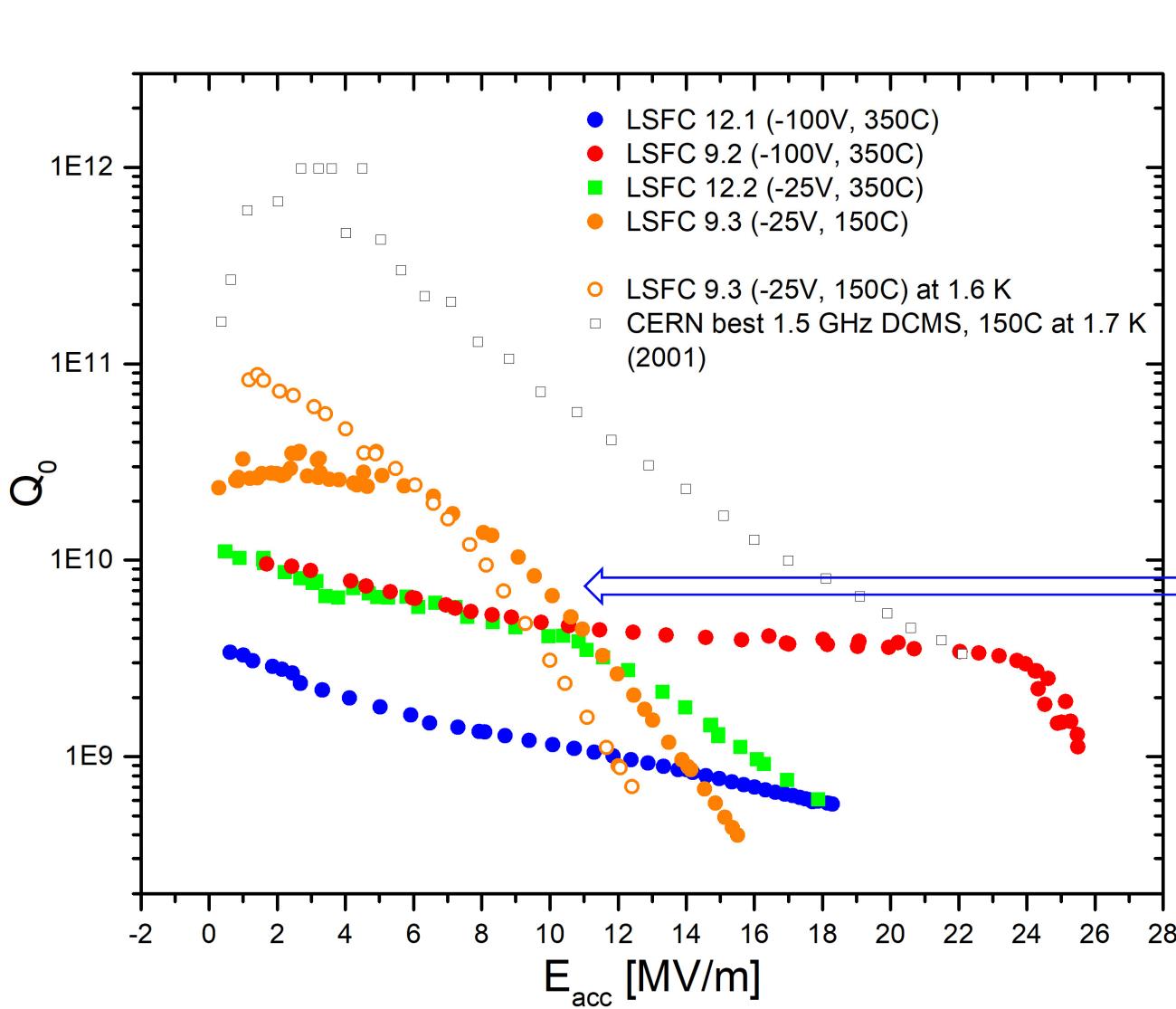
# HiPIMS Cavities RF Behavior



Cool down has significant influence on losses – flux pinning



# HiPIMS Nb/Cu Film RF Results on 1.3 GHz cavities



6 cavities coated  
11 RF test cycles

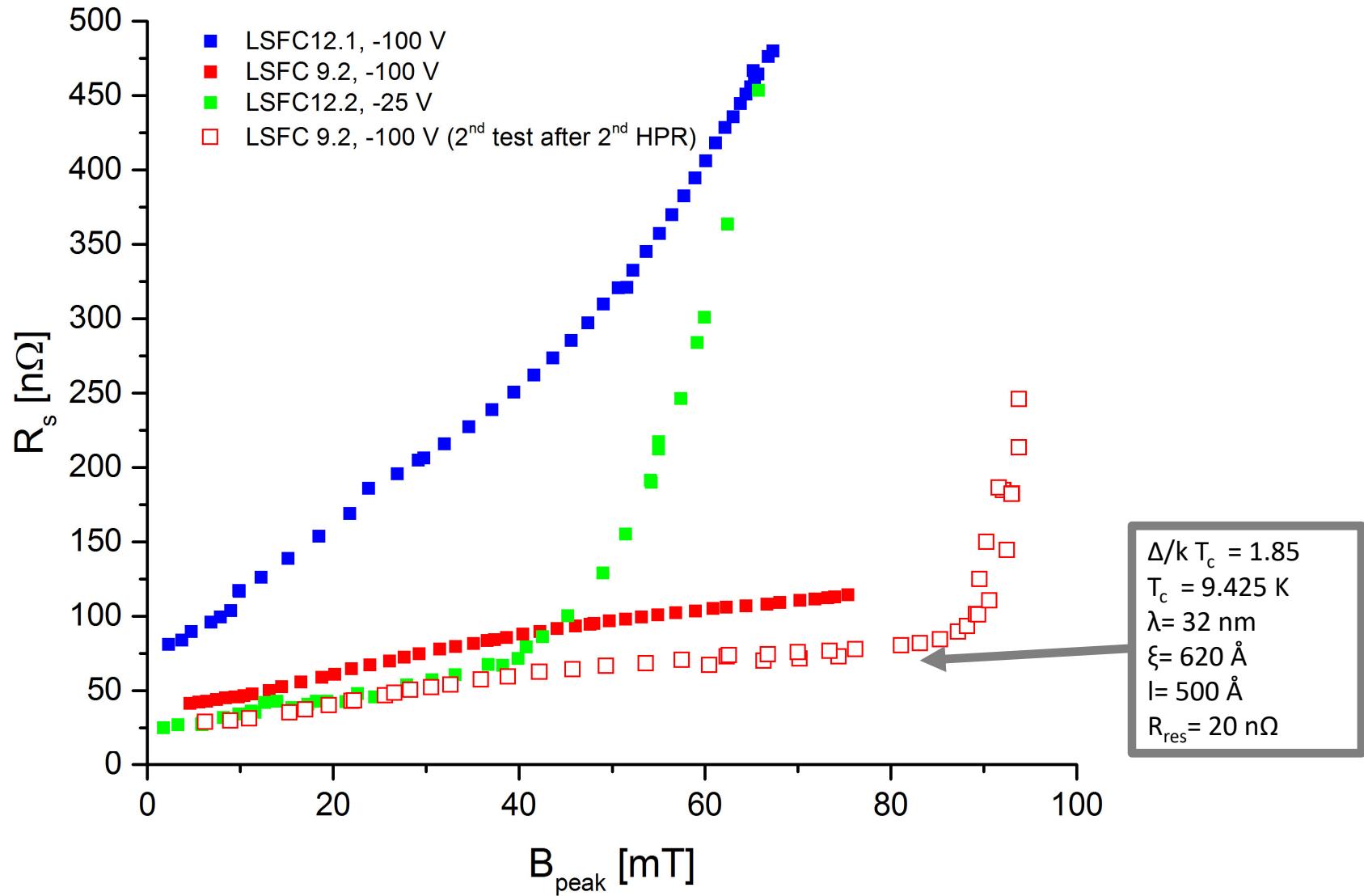
Films sustain HPR at full pressure

Some HiPIMS Nb/Cu cavities show mitigation of the characteristic Q-slope

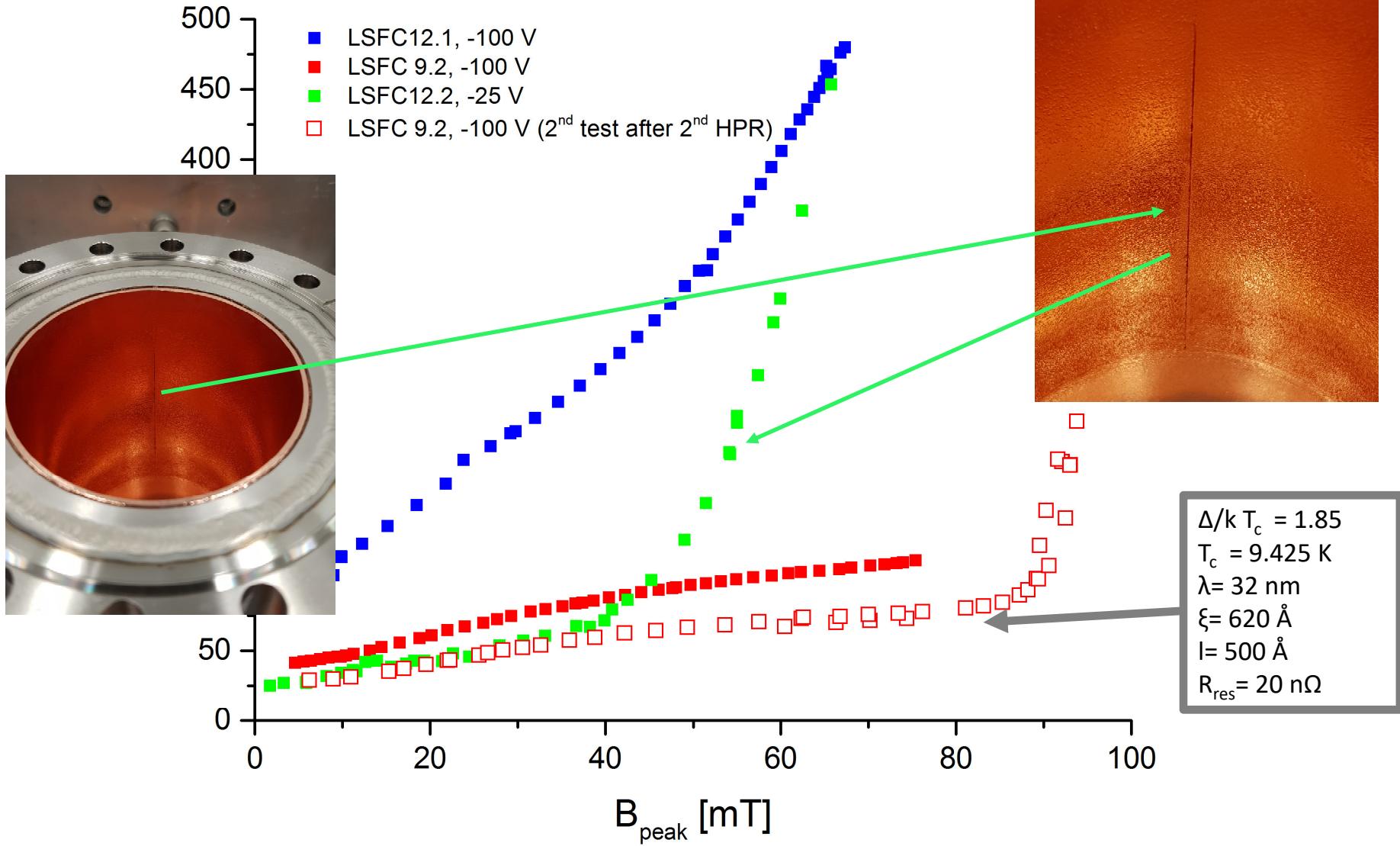
Contamination in system can rapidly degrade RF performance  
(From  $>10^{10}$  to  $5 \times 10^8$ , then  $6 \times 10^7$ ...)



# HiPIMS Cavities – Substrate Quality Issues

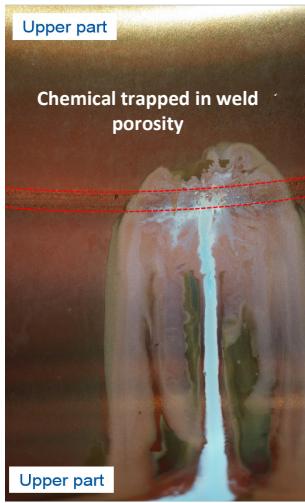


# HiPIMS Cavities – Substrate Quality Issues



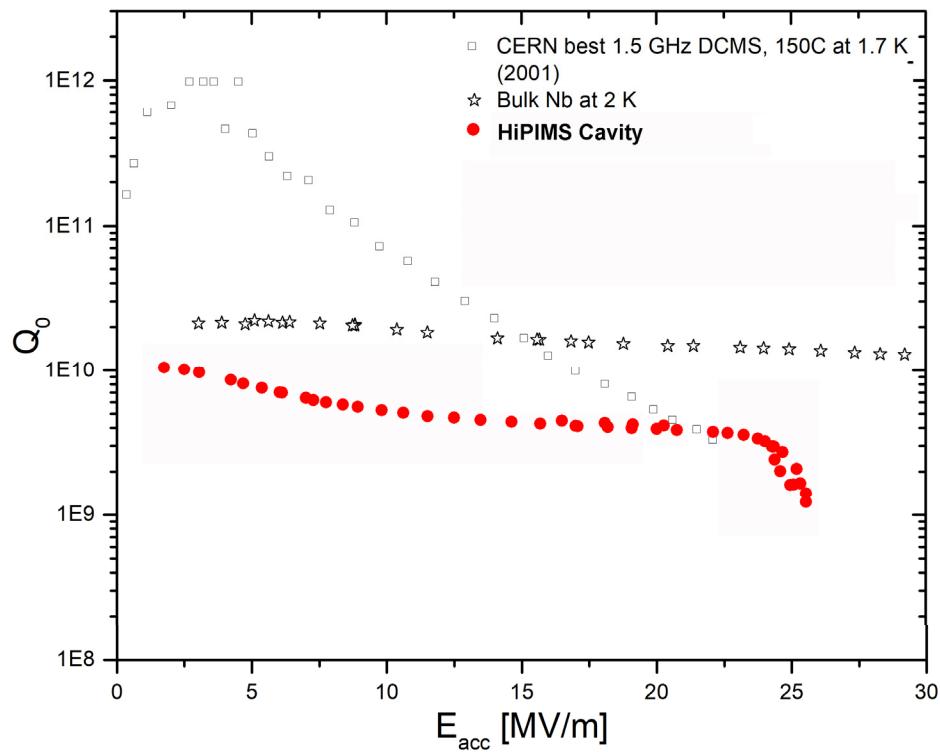
# Cavity Manufacturing Issues

- Cracks on Seam Welds
  - Not visible after welding or CBP
  - Exposed after multiple acid etching cycles
- Effect on Films
  - ❖ Acid trapped potentially leading to film poisoning, delamination ...
  - ❖ Cracks could cause locally thinner films
  - ❖ In extreme cases films so thin that Cu may be uncovered to RF field or film thin enough that RF field can probe Cu underneath



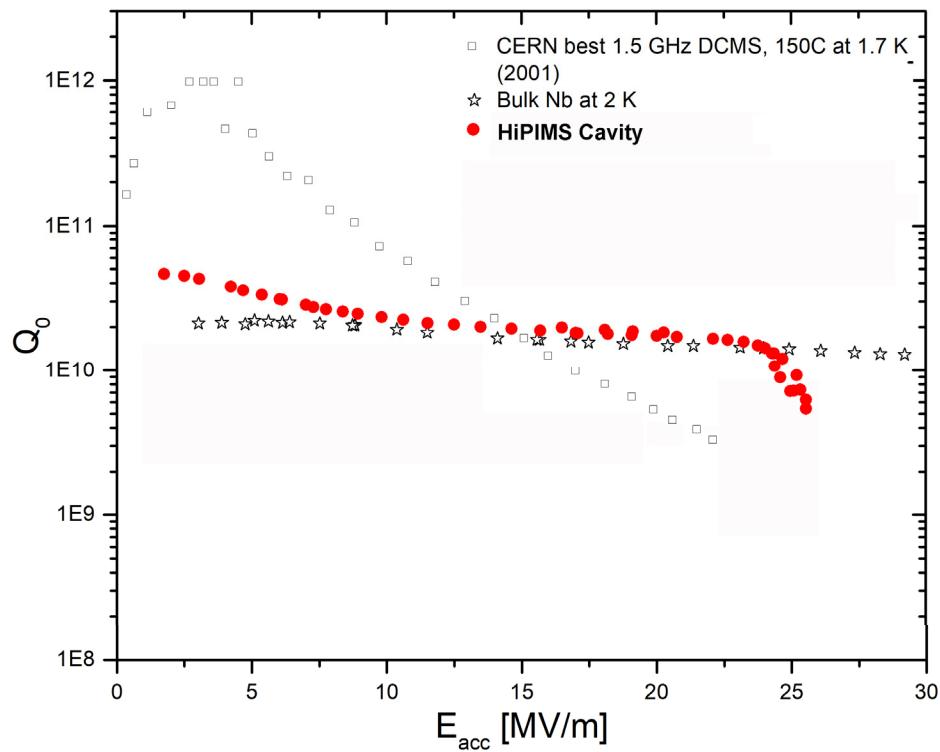
# CONCLUSION & Future Work

## ☐ Mitigation of Q-slope for HiPIMS Cavities



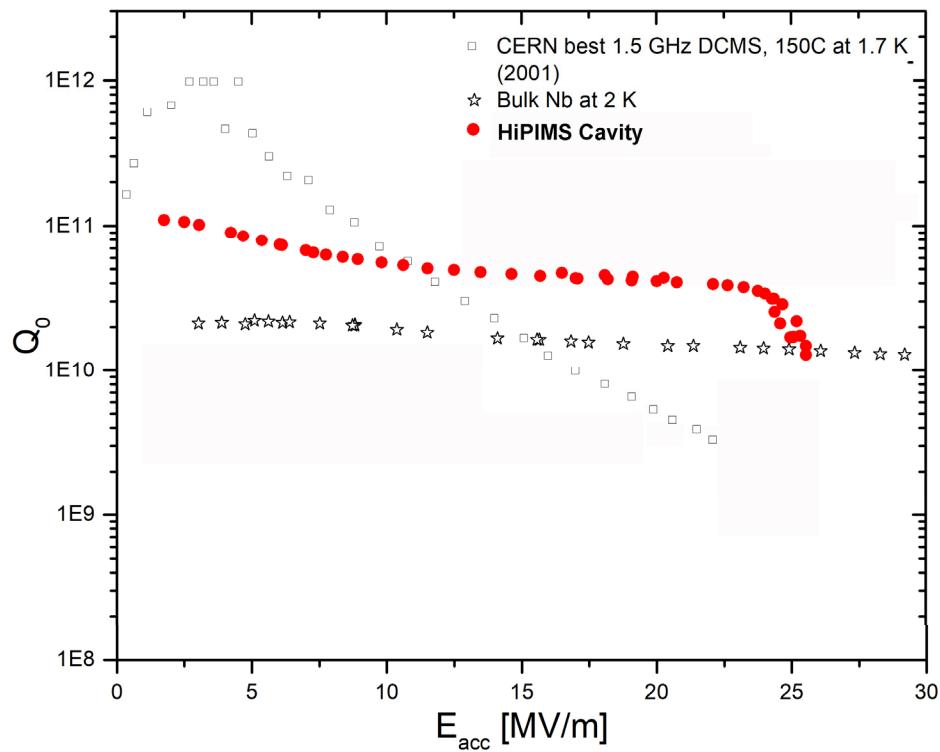
# CONCLUSION & Future Work

## ☐ Mitigation of Q-slope for HiPIMS Cavities



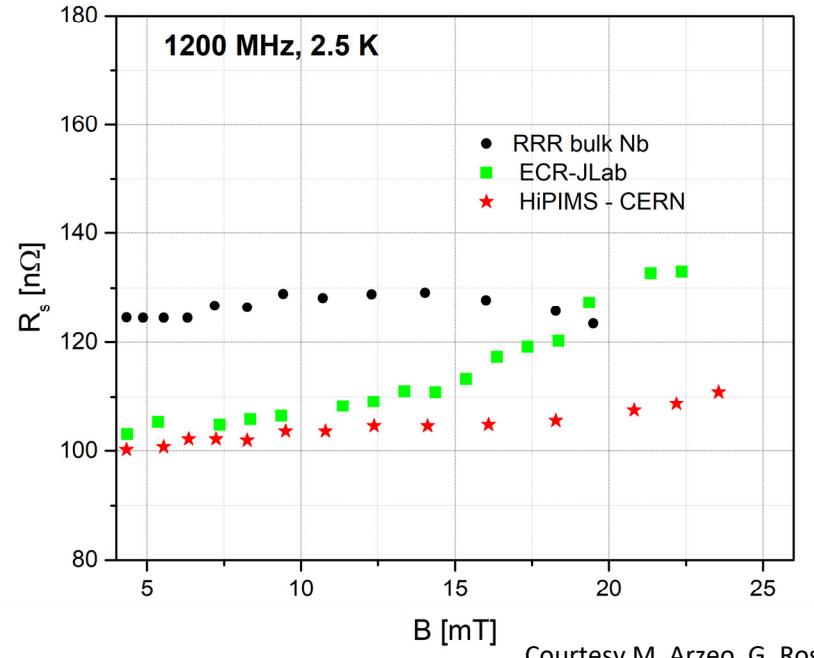
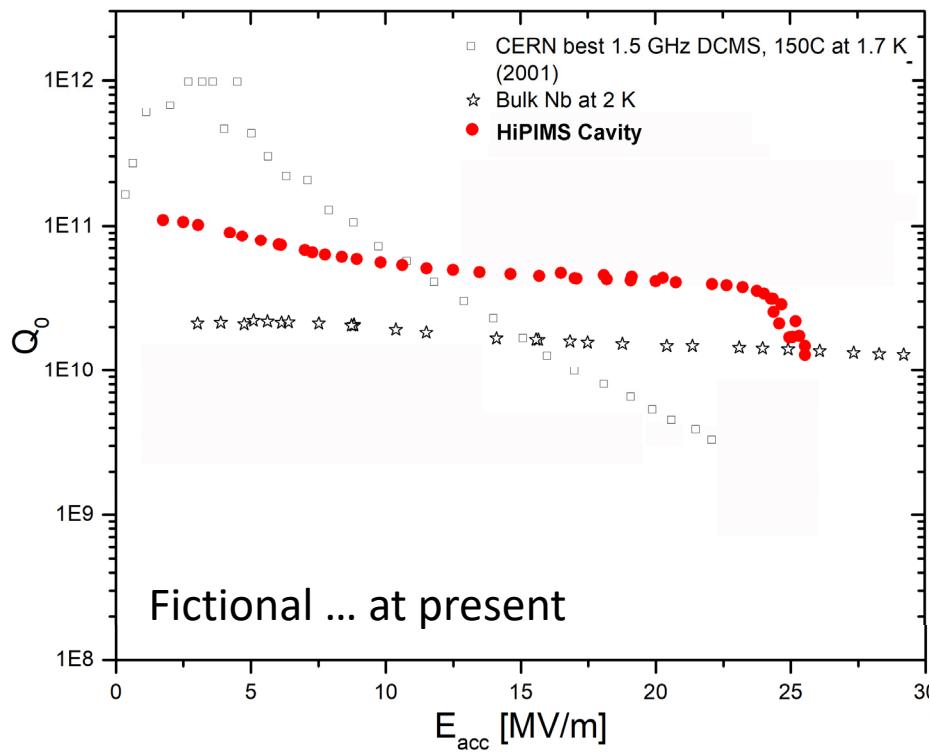
# CONCLUSION & Future Work

## ☐ Mitigation of Q-slope for HiPIMS Cavities



# CONCLUSION & Future Work

## ☐ Mitigation of Q-slope for HiPIMS Cavities

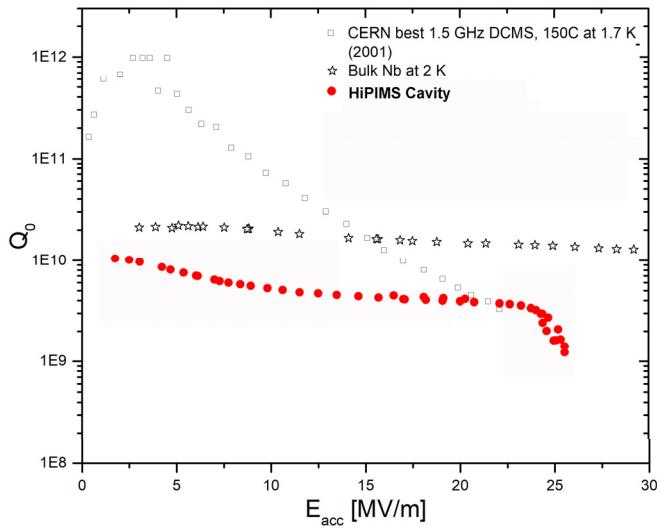


# CONCLUSION & Future Work

## ❑ Mitigation of Q-slope for HiPIMS Cavities

### Principal challenges at present

- ❑ Establish adequate process controls
- ❑ **Need better substrates** see MOP007 (O. Azzolini), FRCAB2 (G. Rosaz)
- ❑ **Need better chemical processes**
  - EP development
- ❑ “Turn the knobs” to truly engineer the SRF surface by manipulating the film growth conditions
- ❑ Deposition on JLEIC cavities (952.6 MHz)



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**DANKE**  
**THANK YOU**